

AMENDMENTS TO THE SPECIFICATION

Page 1, before the first line, please insert the following:

This is national stage application under 35 U.S.C. § 371 of PCT/JP2005/000349 filed on January 14, 2005, which claims priority from Japanese patent application 2004-010844 filed on January 19, 2004, all of which are incorporated herein by reference.

Please replace the paragraph no. [0009] with the following amended paragraph:

It is known that the plasma CVD method can form a film at a relatively low temperature as compared with, for example, the ~~spattering~~sputtering method, thermal CVD method, and catalyst CVD method, and the plasma CVD film shows a good covering of difference in level (step coverage) for device. However, the amount of hydrogen included in the film prepared by the plasma CVD method is relatively large as compared with such methods. Therefore, it is necessary to improve the film forming temperature to some degree or to raise the RF power when it is intended to form a film of which hydrogen content is not more than 30at% as disclosed in the above-mentioned Patent Literature 1. On the other hand, since the organic EL materials have a poor heat resistance in general, there is a possibility that the organic EL materials may be deactivated by the temperature when the protection film is formed with such a low hydrogen content, and thus, the preparation of such a film using the plasma CVD method would be accompanied with a technical difficulty.

Please replace the paragraph no. [0015] with the following amended paragraph:

In addition, a technology which solves the above-mentioned problem is a process for manufacturing an organic electroluminescent device which comprises at least a first electrode, an organic luminescent layer, and an second electrode formed on a substrate, which is characterized

by forming onto the organic electroluminescent device a protection film of which hydrogen content is not less than 30at% through the use of CVD method or ~~spattering~~sputtering method.